

Tuesday Afternoon, November 11, 2014

2D Materials Focus Topic

Room: 310 - Session 2D+AS+HI+MC+NS+PS+SP+SS-TuA

2D Materials Characterization including Microscopy and Spectroscopy

Moderator: Manish Chhowalla, Rutgers University

2:20pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA1 Layer-Dependent Electronic and Physical Structure of 2D van der Waals Crystals, Richard Osgood, Columbia University** **INVITED**

Because of their weak Van der Waals interlayer bonding transition-metal dichalcogenide (TMDC) semiconductors can be fabricated into atomically thin two-dimensional (2D) crystals with substantial ~ 1-2 eV bandgaps. As one example, monolayer MoS₂ consists of a single layer of Mo atoms sandwiched between two layers of S atoms in a trigonal prismatic structure. The TMDC 2D system has attracted great interest because of its distinctive electronic and optical properties, such as (i) a transition from indirect-to-direct band gap in going from the multilayer to monolayer crystal due to a missing interlayer interaction in monolayer form and (ii) strong spin-orbit-coupling-induced split valence bands, i.e. 100's of meV, due to broken inversion symmetry, which makes TMDCs interesting for spin-physics physics and devices. Both properties have been predicted with density functional theory (DFT) calculations and indirectly demonstrated using photoluminescence and Raman spectroscopy.

Recently we have made a series of direct observations of the thickness-dependent electronic-band and crystal structure of TMDCs of both exfoliated and CVD grown sample. Because of the relatively modest sample sizes we have used micrometer-scale, angle-resolved photo-emission spectroscopy (micro-ARPES) of both the exfoliated and chemical-vapor-deposition-grown crystals; these measurements provide direct evidence for the shifting of the valence band maximum from gamma bar (Brillouin zone center) to kappa bar (Brillouin zone corner), as the sample thickness decreases from bulk to monolayer. Our initial results were with MoS₂ and are described in a preliminary way in Refs 1 and 2. Our TMDC experimental results are compared with rigorous DFT calculations of both the bands and the UV transitions matrix elements. The results show an evolution in band structure, which is consistent with an indirect-to-direct bandgap transition in going from few-layer to monolayer TMDC and can be attributed to changes in quantum confinement as the number of layer decreases. Our microARPES and, subsequently, higher resolution nanospectroscopy data provide clear measurements of the hole effective mass, the strain present in the monolayer crystal films, and the valence-band spin-orbit splitting. Our results explain the low hole mobility of monolayer MoS₂ compared to thicker MoS₂ and show clearly the strong orbit split energies. Our results, using nanoLEED and LEEM also provide insight into the structure and defects in monolayer films. Experiments using K-doping of single-crystal samples and resulting level shifts are also described.

1. W. Jin, P.-C. Yeh, N. Zaki, D. Zhang, J. T. Sadowski, A. Al-Mahboob, A. M. van der Zande, D. J. A. Chenet, J. I. Dadap, I. P. Herman, P. Sutter, J. Hone, R. M. Osgood, Jr., "Direct Measurement of the Thickness-Dependent Electronic Band Structure of MoS₂ Using Angle-Resolved Photoemission Spectroscopy." *Phys. Rev. Lett.* **111**, 106801 (2013)

2. Po-Chun Yeh, Wencan Jin, Nader Zaki, Datong Zhang, Jerzy T. Sadowski, Abdullah Al-Mahboob, Arend M. van der Zande, Daniel A. Chenet, Jerry I. Dadap, Irving P. Herman, Peter Sutter, James Hone, and Richard M. Osgood, Jr., "Probing substrate-dependent long-range surface structure of single-layer and multilayer MoS₂ by low-energy electron microscopy and microprobe diffraction," *Phys. Rev. B* **89**, 155408 (2014)

3:00pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA3 X-ray Photoemission and Electron Energy Loss Spectroscopy Investigation of the Band Gap and Band Alignment for h-BN and MoS₂ Materials and Interfaces, Benjamin French, J. Brockman, M. French, M. Kuhn, J.D. Bielefeld, S.W. King, Intel Corporation, E. Bersker, G. Bersuker, SEMATECH, J. DiStefano, Y.C. Lin, J.A. Robinson, Penn State University**

Hexagonal boron nitride (h-BN) and molybdenum disulfide (MoS₂) are two dimensional (2D) materials of significant interest for future nano-electronic devices. Due to a wide band gap (~ 6 eV), close lattice matching (< 2%) and atomic planarity, hexagonal boron nitride (h-BN) is of primary interest as a potential substrate and gate dielectric in graphene channel transistor devices. In contrast, MoS₂ is a 2D semiconducting material with a band gap of ~ 1.8 eV that is attractive as a possible complement or alternative to

graphene for nano-electronic devices requiring a large band gap. A key property for the success of both h-BN and MoS₂ in such devices is the interfacial band alignment with graphene, the gate contact metallization and the surrounding insulating dielectric materials. In this regard, we have utilized x-ray photoelectron spectroscopy (XPS) to determine the Schottky barrier and valence band offsets present at the interfaces between plasma enhanced chemically vapor deposited amorphous h-BN:H and chemically vapor deposited MoS₂. In combination, we have utilized reflection electron energy loss spectroscopy (REELS) to investigate the band gap of both h-BN and MoS₂ materials to deduce the conduction band alignment. We show that in many instances the valence and conduction band offsets are significant and favorable for MoS₂/h-BN transistor devices.

3:20pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA4 STM/STS Characterization of MoS₂ Monolayers and Nanostructures, A. Mills, C. Chen, Virginia Tech, Y. Yu, L. Cao, North Carolina State University, Chenggang Tao, Virginia Tech**

Atomically thin molybdenum disulfide (MoS₂) and nanostructures have been the subject of intense research efforts for their fascinating properties and potential applications in future electronic and optical devices. Especially, monolayer MoS₂, an atomically thin semiconductor with a direct band gap, as opposed to an indirect band gap in bulk MoS₂, has been demonstrated as field effect transistors, optoelectronic devices and chemical sensors. In our experimental study, Monolayer MoS₂ and MoS₂ triangular nanostructures are synthesized through a self-limiting chemical vapor deposition (CVD) approach. The precursor materials, MoCl₅ and sulfur, react at high temperatures to produce MoS₂ species and subsequently precipitate onto substrates to yield MoS₂ films and triangular nanostructures. Using scanning tunneling microscopy (STM), we have investigated the structural and electronic properties of monolayer MoS₂ grown on glassy carbon and triangular MoS₂ nanostructures on highly ordered pyrolytic graphite (HOPG). We will also discuss our scanning tunneling spectroscopy (STS) measurements on these structures.

4:40pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA8 Surface Characterization of Metal Oxide Layers Grown on CVD Graphene and Spin Precession Measurements, Akitomo Matsubayashi, University at Albany-SUNY, W. Nolting, University at Albany-SUNY, D. Sinha, University at Albany-SUNY, A. Jayanthinarasimham, J.U. Lee, University at Albany-SUNY, V.P. LaBella, University at Albany-SUNY**

Ultra thin metal oxide films grown on graphene can be utilized as dielectric barriers between metals and graphene to help isolate a metal contact from the graphene channel for device applications. This is particularly important for graphene based spintronic devices as tunnel barriers between the ferromagnetic metal as a spin injector and graphene have been known to increase the spin relaxation time measured utilizing non-local detection technique of spin precession by avoiding the conductivity mismatch problem. However, simply depositing metal oxide layers such as aluminum oxide on graphene results in non-uniform film lowering the quality of the interface barrier. We will present a systematic study of aluminum oxide layers grown on CVD graphene under ultra-high vacuum conditions with and without titanium seed layers. The aluminum oxide layers with the 0.2 nm titanium seed layers showed reduced surface roughness. The chemical and structural composition determined by XPS will be also presented that shows full oxidation of the aluminum and partial oxidation of the titanium. The I-V characteristic study performed to electrically evaluate the metal oxide and the preliminary results of non-local spin precession measurements will be also addressed.

5:00pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA9 Morphology of CVD-grown Hexagonal Boron Nitride on Cu Foils, Karthik Sridhara, W.G. Cullen, University of Maryland, College Park, J.K. Hite, Naval Research Laboratory, M.S. Fuhrer, Monash University, Australia, D.K. Gaskill, B.N. Feigelson, Naval Research Laboratory**

Hexagonal boron nitride (h-BN) has grown into prominence as a dielectric for graphene heterostructures. h-BN and graphene have been grown using chemical vapor deposition on various transition metal substrates. Compared to graphene, the morphology of CVD-grown h-BN on Cu has not been as widely studied. Here, we present a systematic study of the morphology of hexagonal boron nitride (h-BN) grown on polycrystalline Cu foils by chemical vapor deposition. The growth of h-BN is performed at ~1000°C in atmospheric pressure CVD with Ammonia Borane (H₃NBH₃) as the precursor. The copper foils, used as catalytic substrates, are thermally annealed at ~1030°C for >5 hours prior to growth and cooled slowly following growth termination. We utilized Ultra-high vacuum Scanning Tunneling Microscopy (STM), ambient AFM and SEM to assess the morphology of the CVD grown h-BN films. Highly symmetric single

crystallites of h-BN are observed for sub-monolayer growth, in agreement with recent reports. We consistently observe a corrugated topographic structure within the h-BN crystallites which is distinctly different from the surrounding copper surface, and this is consistently seen in STM, AFM, and high-resolution SEM. Our aim is to understand the nature of this difference and whether it might be due to effects of differential thermal contraction between h-BN and copper. However, complications arise due to possible changes in the copper substrate topography post-growth due to surface oxidation of the copper. Preliminary results with lateral force microscopy (LFM, frictional mode) show that these corrugations are unidirectional in a single Cu grain irrespective of the orientation of the h-BN crystal and generate frictional forces 200% greater than on the surrounding copper surface, reminiscent of earlier reports of unique frictional behavior in atomically-thin membranes [1]. STM and AFM are also used to study the twin crystal boundaries of h-BN. Preliminary STM observations indicate that merging h-BN crystals consistently have a gap of about 5 nm between them. The results of this study are independent of small variations of growth conditions.

References:

[1] C. Lee, Q. Li, W. Kalb, X.-Z. Liu, H. Berger, R. Carpick, and J. Hone, "Frictional characteristics of atomically thin sheets," *Science* (New York, N.Y.), vol. 328, no. 5974, pp. 76–80, 01-Apr-2010.

5:20pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA10 Influence of Chemisorbed Oxygen on the Growth of Graphene on Cu(100) and Cu(111) by Chemical Vapor Deposition, EngWen Ong**, University at Albany-SUNY, Z.R. Robinson, U.S. Naval Research Laboratory, T.R. Mowll, P. Tyagi, University at Albany-SUNY, H. Geisler, SUNY College at Oneonta, C.A. Ventrice, Jr., University at Albany-SUNY

The influence of chemisorbed oxygen on the growth of graphene by catalytic decomposition of ethylene in an ultra-high vacuum (UHV) chamber on both the Cu(100) and Cu(111) surfaces has been studied. A custom UHV compatible heater stage was constructed that allows heating of a crystal to temperatures as high as 1000 °C at hydrocarbon pressures of up to 100 mTorr. System recovery to the low 10^{-10} Torr range is achieved within a few minutes of opening the gate valve to the turbo pump. The crystal structure of the graphene films was characterized with in-situ low energy electron diffraction (LEED), and the growth morphology was monitored by ex-situ scanning electron microscopy (SEM). For the clean Cu(100) substrate, heating from room temperature to the growth temperature while dosing with ethylene resulted in the formation of epitaxial graphene films. The crystal quality was found to depend strongly on the growth temperature. At 900 °C, well-ordered two-domain graphene films were formed. For the Cu(111) surface, heating from room temperature to the growth temperature while dosing with ethylene did not result in the formation of graphene. This is attributed to the lower catalytic activity of the (111) surface and the relatively high vapor pressure of the Cu surface. The use of an Ar overpressure to suppress Cu sublimation during the growth resulted in the formation of predominately single-domain epitaxial graphene films. Predosing either the Cu(100) or Cu(111) surface with a chemisorbed layer of oxygen before graphene growth was found to adversely affect the crystal quality of the graphene overlayers by inducing a much higher degree of rotational disorder of the graphene grains with respect to the substrate. The SEM analysis revealed that the nucleation rate of the graphene islands dropped by an order of magnitude after predosing either the Cu(100) or Cu(111) surface with a chemisorbed oxygen layer before growth. On the other hand, the average area of each graphene island was observed to increase by at least an order of magnitude. Therefore, the presence of oxygen during graphene growth affects both the relative orientation and average size of grains within the films grown on both substrates.

5:40pm **2D+AS+HI+MC+NS+PS+SP+SS-TuA11 Novel Materials Properties at Atomically Thin Limit, Zhi-Xun Shen**, Stanford University
INVITED

In this talk, I will discuss recent progresses in uncovering novel materials properties at ultra-thin limit, with focus on mono-unit-cell superconductor FeSe and semiconductor MoSe₂ respectively.

The observation of a large superconducting-like energy gap which opens at temperatures up to 65 K in single unit cell (1UC) thick iron selenide films on SrTiO₃(FeSe/STO) has generated tremendous interest. A challenge is to understand the cause of enhanced Cooper pairing strength in this system, and possibly increase superconducting T_c. In this talk, we show angle-resolved photoemission spectroscopy, mutual inductance, and other measurements on 1UC and multi-UC thick FeSe films grown on Nb-doped SrTiO₃. Our data provide clear evidence for strong cross-interface electron-phonon coupling in single UC, raising the possibility that large pairing gap are caused by the strong coupling between the FeSe electrons and certain

collective modes of SrTiO₃. This suggests a pathway of "integrated functional components" approach to boost superconducting properties.

The intense interest of quantum systems in confined geometries is further amplified by the recent discovery of large enhancement in photoluminescence quantum efficiency and a potential route to "valleytronics" in atomically thin layered transition metal dichalcogenides (TMDs) MX₂ (M = Mo, W; X = S, Se, Te), which are closely related to the indirect to direct band gap transition in the single layer limit. Using angle-resolved photoemission spectroscopy (ARPES) on high quality thin film samples of MoSe₂ grown by molecular beam epitaxy (MBE), we have made a direct observation of a distinct transition from indirect to direct band gap as the thickness of the sample is reduced to a monolayer. The experimental band structure indicates a stronger tendency of monolayer MoSe₂ towards direct band gap with larger gap size than theoretical prediction. A comparison of directly measured ARPES band gap and optical data led to important new insights on semiconductor physics in 2D. Moreover, our finding of a significant spin-splitting of ~180meV at the valence band maximum (VBM) of a monolayer MoSe₂ film could greatly expand its possible application in spintronic devices.

If time permits, I will also discuss the superconductivity in CaC₆ and its implication on a possible pathway for superconducting graphene.

Wednesday Afternoon, November 12, 2014

In-Situ Spectroscopy and Microscopy Focus Topic Room: 313 - Session IS+2D+MC+NS+SP+SS-WeA

In-Situ Scanning Microscopy

Moderator: Markus Ammann, Paul Scherrer Institut

2:20pm IS+2D+MC+NS+SP+SS-WeA1 *In Situ* Studies of Model Fuel Cells, *Zhi Liu*, Lawrence Berkeley National Laboratory **INVITED**

The ambient pressure x-ray photoelectron spectroscopy (AP-XPS) endstations based on differentially pumped electron energy analyzers have been recognized by scientific communities as an important in-situ tool to study water, environmental science, catalysis and many other important fields. Multiple new AP-XPS endstations are currently under planning or development at US and international synchrotron light sources. Recently we have installed a new hard x-ray AP-XPS endstation at ALS Beamline 9.3.1 (2.5keV- 5keV). By using X-ray up to 5KeV, we can perform AP-XPS at a pressure up to 110 torr. The probing depth of photoelectrons also increases to >10 nm, which will allow us to study not only the gas/solid interface but also the liquid/solid interface. In this talk, I will give an overview of science projects at ALS BL9.3.2 in heterogeneous catalysis and electro-chemistry using these new systems. Furthermore, I will present results of our in-situ study on the electrolyte/electrode interface of a working model electrochemical cell at ALS BL9.3.1. We believe the successful development of soft and hard X-ray APXPS endstations will provide energy research community a powerful in-situ tool to directly study the electrolyte/electrode interface of many important electrochemical devices.

3:00pm IS+2D+MC+NS+SP+SS-WeA3 Probing of Nanoscale Objects in Reactive Liquids through Membranes using Near-Field Microwave Microscopy, *Alexander Tselev*, Oak Ridge National Laboratory, *A. Komakov*, National Institute of Standards and Technology (NIST)

Many functional objects (and interfaces) have to be studied in situ when the object is immersed in liquid environment. In addition, for energy, chemical, (bio-) medical and other applications, there is a need to study the encapsulated objects, which otherwise can be chemically reactive or toxic. These samples are often mesoscopically small or exist in minuscule quantities. Recently, we have developed a process for preparation of liquid-filled cells sealed with ultrathin membranes. Such cells can be implemented for in-situ studies using, for example, electron or soft x-ray microscopy due to a high transparency of these membranes to electron beams. However, in many cases electron microscopy is an invasive technique due to various electron beam induced parasitic effects (e.g. radiolysis or beam induced deposition). To overcome these impediments, we demonstrate the scanning microwave impedance microscopy (sMIM) to image different nanoscale objects immersed in the liquid environment through 30 nm SiN membranes. In the sMIM, microwaves of a frequency of 3 GHz are sent through a coaxial cable connected to a shielded cantilever probe fully compatible with an AMF microscope. The sharp probe tip provides "focusing effect" for the electric component of the microwave. For imaging, the tip is brought into gentle mechanical contact with a membrane. Amplitude and phase of microwaves reflected from the probe are monitored. Since the wave reflection is dependent on the tip-sample system impedance, reflected waves carry information about sample local properties. The effective distance into the sample depth, where the tip-induced field enhancement takes place, is approximately equal to the tip apex radius. Since the membrane thickness is smaller compared to the tip radius of a typical probe (about 50 nm for a fresh tip), the tip-sample impedance is dependent on the dielectric properties of the material beneath membrane, and therefore, it is possible to "see" through the membrane. We demonstrate imaging of different combinations of model liquids and nanoparticles: water and water-based solutions ($\epsilon \sim 80$), organic solvents ($\epsilon \sim 10-25$), and oils ($\epsilon \sim 2-3$) containing Ni metal, polystyrene ($\epsilon \sim 2.5$) and PbO ($\epsilon \sim 25$) particles. This technique can be further implemented for a broad range of objects in confined liquids, and can be used to monitor interfacial electrochemical reactions. Imaging with sMIM was performed at CNMS, which is sponsored at ORNL by the SUFD, BES, US DOE.

4:20pm IS+2D+MC+NS+SP+SS-WeA7 Caught in the Act! Live Observations of Catalysts Using High-Pressure Scanning Probe Microscopy, *Irene Groot*, Huygens-Kamerlingh Onnes Laboratory, Leiden University, Netherlands **INVITED**

Recently it has become clear that essential differences can exist between the behavior of catalysts under industrial conditions (high pressure and temperature) and the (ultra) high vacuum conditions of traditional laboratory experiments. Differences in structure, composition, reaction

mechanism, activity, and selectivity have been observed. These observations indicated the presence of the so-called pressure gap, and made it clear that meaningful results can only be obtained at high pressures and temperatures. However, most of the techniques traditionally used to study catalysts and their reactions were designed to operate under (ultra) high vacuum conditions. To bridge the pressure gap, the last years have seen a tremendous effort in designing new instruments and adapting existing ones to be able to investigate catalysts *in situ* under industrially relevant conditions.

This talk focuses on the development of scanning probe microscopy for *operando* observations of active model catalysts. In our group, we have developed set-ups that combine an ultrahigh vacuum environment for model catalyst preparation and characterization with a high-pressure flow reactor cell, integrated with either a scanning tunneling microscope or an atomic force microscope. With these set-ups we are able to perform atomic-scale investigations of well-defined model catalysts under industrial conditions. Additionally, we combine the structural information from scanning probe microscopy with time-resolved mass spectrometry measurements on the gas mixture that leaves the reactor. In this way, we can correlate structural changes of the catalyst due to the gas composition with its catalytic performance.

This talk highlights a short overview of the instruments we developed and illustrates their performance with results obtained for different model catalysts and reactions. As a proof of principle, results for the fruit fly of surface science, *i.e.* CO oxidation, will be shown. But additionally, results for more complex reactions such as NO reduction, Fischer-Tropsch synthesis, desulphurization, and production of chlorine will be discussed.

5:00pm IS+2D+MC+NS+SP+SS-WeA9 X-ray Photoelectron Spectroscopy Studies of H₂O Dissociation on Pre-oxidized Al (111) and Cu (111) Single Crystal Surface, *Qianqian Liu*, SUNY, Binghamton University, *X. Tong*, Brookhaven National Laboratory, *G.W. Zhou*, SUNY, Binghamton University

Dissociation of H₂O molecules on ultrathin oxide overlayers formed on metal surfaces plays a critical role in many catalytic reactions. However, the effects of chemical states and thickness of oxide overlayers on the microscopic process of H₂O dissociation are still poorly understood. In this work, X-ray photoelectron spectroscopy (XPS) is employed to study H₂O dissociation on oxidized Al (111) and Cu (111) surfaces with controlled chemical states and thicknesses of the oxide films. For Al (111), the experiment was performed under two water vapor pressures (10⁻⁶ Torr and 5 Torr) on aluminum oxide films with the thicknesses varying from 2.47 Å to 5.14 Å; for Cu (111), the experiment was performed by varying the water vapor pressure from 10⁻⁷ Torr to 10⁻⁵ Torr and temperature from 100°C to 450°C on the oxide film with a constant thickness. Al (2p), Cu (2p), Cu (LMM) and O (1s) spectra were monitored by XPS after each oxygen exposure followed by subsequent H₂O exposure. Upon exposing the oxide to water vapor, the O (1s) peak shifts to a higher energy and becomes broader. A detailed analysis of the spectra indicates that H₂O molecules dissociate into OH groups for both oxidized Al and Cu surfaces. However, the subsequent reaction of OH groups with the oxide films on Cu (111) and Al (111) surfaces are dramatically different. On the oxidized Al(111) surface, OH is further incorporated into the aluminum oxide that results in the thickening of the oxide film, whereas on the oxidized Cu (111) surface, OH works as a reducing agent to remove oxygen from the oxide film that results in the thinning of the Cu oxide film. The microscopic processes underlying the differences in H₂O dissociation on oxidized Al (111) and Cu (111) will be described in detail.

5:20pm IS+2D+MC+NS+SP+SS-WeA10 Operando APXPS of the Liquid-Solid Interface: Au Oxidation, *Ethan Crumlin*, *S.A. Axnanda*, *P.N.R. Ross*, *Z.L. Liu*, Lawrence Berkeley National Laboratory

Interfaces play an important role for many reaction processes and are essential for electrochemistry. Electrochemical systems ranging from high temperature solid oxide fuel cells (SOFC) to lithium ion batteries to capacitors have a wide range of important interfaces between solids, liquids, and gases which play a pivotal role in how energy is stored, transferred, and/or converted. Previous capabilities of ambient pressure X-ray Photoelectron Spectroscopy (APXPS) have primarily only been able to observe the gas-solid and gas-liquid interfaces. However, recent enhancements now enable new APXPS systems to work at pressures larger than 20 Torr, and utilize 'Tender' X-rays (2.5 – 7 keV). These features provide new capabilities and opportunities for probing the liquid-solid and solid-solid interfaces. Using synchrotron X-rays at Lawrence Berkeley National Laboratory, the Advanced Light Source and our 'Tender' X-ray APXPS endstation that is outfitted with various *in situ/operando* features such as electrical leads to apply electrical potentials and operates at

pressures >20 Torr, to observe the liquid-solid interface of a gold foil electrode that has been immersed and partially removed from a liquid electrolyte. This talk will provide details on how we used this technique to probe liquid-solid interface and in real-time observe the oxidation of the gold foil electrode under varying applied potentials and different electrolyte solutions.

5:40pm **IS+2D+MC+NS+SP+SS-WeA11 Water on ZnO(10-10) Investigated by Ambient Pressure X-ray Photoelectron Spectroscopy**, *Chris Goodwin*, University of Delaware, *A. Boscoboinik*, Brookhaven National Lab, *C. Arble, J.T. Newberg*, University of Delaware

The extent to which ZnO hydroxylates under ambient conditions can significantly influence catalytic properties. Thus, it is critical to understand the composition of different ZnO terminations as a function of relative humidity (RH) in order to elucidate the true interfacial surface terminations. In this talk we present results of ambient pressure XPS (APXPS) for water exposures to a ZnO(10-10) single crystal. It will be shown that ZnO(10-10) extensively hydroxylates at the interface, and both molecular and dissociative water increase as the RH increases. These results are consistent with simulations in the literature that highlight the efficacy for ZnO(10-10) to dissociate water.

Scanning Probe Microscopy Focus Topic Room: 312 - Session SP+AS+BI+NS+SS-WeA

Advances in Scanning Probe Microscopy
Moderator: Tae-Hwan Kim, Pohang University of Science and Technology, Jewook Park, Oak Ridge National Laboratory

2:20pm **SP+AS+BI+NS+SS-WeA1 Majorana Mode in Vortex core of $\text{Bi}_2\text{Te}_3/\text{NbSe}_2$ Topological Insulator-Superconductor Heterostructure**, *Jinfeng Jia*, Shanghai Jiao Tong University, China **INVITED**

Majorana fermions have been intensively studied in recent years for their importance to both fundamental science and potential applications in topological quantum computing^{1,2}. Majorana fermions are predicted to exist in a vortex core of superconducting topological insulators³. However, they are extremely difficult to be distinguished experimentally from other quasiparticle states for the tiny energy difference between Majorana fermions and these states, which is beyond the energy resolution of most available techniques. Here, we overcome the problem by systematically investigating the spatial profile of the Majorana mode and the bound quasiparticle states within a vortex in $\text{Bi}_2\text{Te}_3/\text{NbSe}_2$ ⁴ by using *in situ* ultra-low temperature STM/STS. While the zero bias peak in local conductance splits right off the vortex center in conventional superconductors, it splits off at a finite distance ~ 20 nm away from the vortex center in $\text{Bi}_2\text{Te}_3/\text{NbSe}_2$, primarily due to the Majorana fermion zero mode. While the Majorana mode is destroyed by reducing the distance between vortices, the zero bias peak splits as a conventional superconductor again. This work provides strong evidences of Majorana fermions and also suggests a possible route to manipulating them.

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3. L. Fu, C. L. Kane, Phys. Rev. Lett. 100, 096407 (2008).
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* In cooperation with Jin-Peng Xu, Mei-Xiao Wang, Zhi Long Liu, Jian-Feng Ge, Xiaojun Yang, Canhua Liu, Zhu An Xu, Dandan Guan, Chun Lei Gao, Dong Qian, Ying Liu, Qiang-Hua Wang, Fu-Chun Zhang, Qi-Kun Xue

3:00pm **SP+AS+BI+NS+SS-WeA3 Robust Protection from Backscattering in the Topological Insulator $\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$** , *Fumio Komori, S. Kim, S. Yoshizawa, Y. Ishida*, University of Tokyo, Japan, *K. Eto, K. Segawa*, Osaka University, Japan, *S. Shin*, University of Tokyo, Japan, *Y. Ando*, Osaka University, Japan

Three-dimensional (3D) topological insulators (TIs) are accompanied by gapless surface states due to a nontrivial Z_2 topology of the bulk wave functions. The topological surface state (TSS) of a 3D TI is helically spin polarized, which leads to a suppression of electron scatterings due to spin mismatch between the eigenstates before and after the scattering. The suppression has been inferred from the measurements of quasiparticle interference (QPI) using scanning tunneling microscopy. No QPI was

observed for intraband scatterings within unwarped TSSs. However, it has not been clear to what extent the scattering is suppressed within TSS.

In the present study, we have elucidated how the elastic scattering is suppressed as a function of the scattering angle and electron energy in the helically-spin-polarized surface electrons in a single and unwarped upper Dirac cone of $\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$. In this material [1], E_F is located very close to the Dirac energy E_D . We compared the scattering wave vectors observed at 5 K with the diameters of the constant-energy contours of the unoccupied TSS which was measured by using time-resolved ARPES implementing a pump-probe method. Moreover, the inelastic scattering time of unoccupied TSS was directly obtained by this method.

At the energy above E_D , we found that there is a sharp threshold for the length of the scattering vector, above which the observed QPI intensity is abruptly diminished [2]. Such a threshold indicates the existence of a well-defined critical scattering angle beyond which elastic scattering is suddenly suppressed. The observed protection from backscattering in the TSS occurs not only for 180° but also for a wide range of angles between 100° and 180° . Such a wide angle range for the protection from backscattering is found to be essentially independent of the energy up to 300 meV above E_D until the Dirac cone becomes warped and/or the bulk scattering events intervene. At energies higher than 300 meV, we found hexagonal patterns in the FT-QPI images that come from warping of the TSS Dirac cone. In this energy range, the critical scattering vector was not clearly observed, indicating a different mechanism of the protection from backscattering in the warped Dirac cone. The observed inelastic scattering lifetime of TSS is longer than 10 psec just above E_F . The robust protection from the backscattering and long inelastic scattering in the TSS strongly support the possible applications for electronics and spintronics using weak electron scattering of TSS at E_F .

References

1. A. A. Taskin *et al.*, Phys. Rev. Lett. **109**, 066803 (2012).
2. S. Kim, *et al.*, Phys. Rev. Lett. **112**, 136802 (2014).

3:20pm **SP+AS+BI+NS+SS-WeA4 Measurements and Analysis of Sub Nanometer Stepped Surfaces Using a Traceable Atomic Force Microscope**, *Ndubuisi Orji*, National Institute of Standards and Technology (NIST), *S. Gonda*, AIST, Japan, *R.G. Dixson*, National Institute of Standards and Technology (NIST)

Although scanning probe microscopes are used in a wide variety of nanoscale measurements, the issue of instrument characterization, accuracy and calibration, continue to be a limiting factor in interpreting the resulting data. In order to accurately characterize dimensional linearity and accuracy at the sub-nanometer range, samples and robust analysis techniques suited to measurements at this range should be used.

Using Al_2O_3 surfaces on the c(0001), a(110), and r(102) planes, and robust analyses techniques, we evaluate stepped surfaces for linearity characterization at the nanoscale. Measurements were performed using a traceable atomic force microscope (T-AFM) with displacement interferometry in all three axes. The T-AFM, which has a metrology scanning stage monitored in six axes, is housed in a mini environment with a long term temperature range of less than 2 mK, and serves as a stable platform to develop calibration standards.

The smallest of the features Al_2O_3 c(0001) with a height of 0.22 nm shows a combined uncertainty of 0.01 nm, with a linearity of 0.009%. The intrinsic traceability of the T-AFM (through displacement interferometer to the S_I meter) provides additional verification to the size naturally occurring steps of the Al_2O_3 and other samples used. The results show that robust and stable linearization and calibration procedures could be developed for sub nanometer SPM characterization with low uncertainty. This will enable and support accurate dimensional characterization of scientifically relevant surfaces.

4:20pm **SP+AS+BI+NS+SS-WeA7 Direct Observation of Edge States of 1D and 2D Topological insulators**, *Han Woong Yeom*, Institute for Basic Science, Republic of Korea **INVITED**

1D and 2D topological insulators (TI's) are characterized by 0D and 1D edge states of exotic spin-charge characteristics. In this talk, we introduce the first direct real space observations of such 0D and 1D edge channels of 1D and 2D TI's by scanning tunneling microscopy/spectroscopy. The 1D TI utilized is the charge density wave phase of In atomic wires formed on the Si(111) surface, which we discovered in 1999. We clearly identified, topographically and spectroscopically, two different soliton excitations along the wires. The unique features of these solitons, theoretically unraveled as chiral solitons of the Z_4 topology, are discussed. On the other hand, a Bi(111) bilayer was theoretically predicted as a 2D TI in 2005. We have grown Bi(111) bilayer nanoislands with zigzag edges on the surface of $\text{Bi}_2\text{Te}_2\text{Se}$. Along those edges, we identified the edge localized electronic state in accordance with first principle calculations. The unexpected

electronic structures of the epitaxial Bi(111) bilayer and the Bi/Bi₂Te₂Se interface are discussed. These two findings pave the avenue towards the microscopic study and the nanoscale utilization of topological solitons and quantum spin Hall states.

5:00pm **SP+AS+BI+NS+SS-WeA9 Controlling Charges of the Dipole Layer at Metal-Semiconductor Interfaces**, *Tae-Hwan Kim*, Pohang University of Science and Technology, Republic of Korea, *H.W. Yeom*, Pohang University of Science and Technology and Institute for Basic Science, Republic of Korea

Metal-semiconductor interfaces have drawn a lot of interest in the field of semiconductor surface and interface science, and have been one of the most essential parts in semiconductor electronic and optoelectronic devices. For example, the Schottky-barrier height experimentally observed at the metal-semiconductor interface appears to be nearly independent of the work function of the metal. Since the time of Bardeen, interface gap states seem to have been a primary mechanism of the Schottky-barrier height causing Fermi level pinning at metal-semiconductor interfaces. Recently, polarized chemical bonds at metal-semiconductor interfaces have been recognised to lead to the apparent Fermi level pinning effect. When these interface bonds are formed underneath thin metal islands grown on a silicon substrate, a spontaneous charge transfer across the semiconductor-metal interfaces occurs as a result of the difference in the Fermi level positions between the metal and the semiconductor. These polarized chemical bonds can form a dipole layer. This dipole layer can play an important role in many areas of technology, for instance, in organic light emitting diodes. However, some of the fundamental aspects of the charge injection process into/from the interface dipole layer at the Schottky contact are yet not explored in any real detail.

In this work, we report the use of scanning tunneling microscopy (STM) to form a double-barrier tunneling junction (DBTJ) with thin metallic nanoislands grown on Si(111) and to control charges of the interface dipole layer formed between the metallic nanoislands and the Si(111) substrate. Reversible hysteric switchings in their $I-V$ and differential conductance spectra are observed due to the charging and discharging of the interface dipole layer in a similar fashion to molecular DBTJs. STM images clearly visualize the distinct charge states and scanning tunneling spectroscopy (STS) spectra reveal that quantum well states (QWSs) of the ultrathin islands act as the charging/discharging channels in analogy to the molecular orbitals in the case of the molecular DBTJs. This work demonstrates that the charges of the interface dipole layer at the nanoscale Schottky contact can be controlled by the electron transfer via the QWSs of the metallic islands.

5:20pm **SP+AS+BI+NS+SS-WeA10 Advances in Imaging and Quantification of Electrical Properties at the Nanoscale using Scanning Microwave Impedance Microscopy (sMIM)**, *Stuart Friedman*, *Y. Yang*, *O. Amster*, PrimeNano, Inc, *S. Johnston*, Stanford University

Scanning Microwave Impedance Microscopy (sMIM) is a novel mode for AFM-enabling imaging of unique contrast mechanisms and measurement of local permittivity and conductivity at the 10's of nm length scale. Custom shielded AFM probes enable the system to use microwaves to probe the impedance of the tip sample interface and extract information on local electrical properties of the sample. After introducing the theory of operation, we will review the state of the art, including imaging studies of microelectronic devices as well as novel materials and nanostructures, such as graphene and patterned optical crystals and ferro-electrics. These studies reveal novel information about doping distributions, domains, domain walls and other features. In addition to imaging, the technique is suited to a variety of metrology applications where specific physical properties are determined quantitatively. We will present research results on quantitative measurements of dielectric constant (permittivity) and conductivity (e.g. dopant concentration) for a range of materials. For samples where properties such as dielectric constant are known the technique can be used to measure film thickness.

5:40pm **SP+AS+BI+NS+SS-WeA11 Scanning Photocurrent Microscopy on MoS₂, MoS_{2(1-x)Se_{2x}}, and MoSe₂ Monolayer Islands and Films Grown by CVD**, *Velveth Klee*, *D. Barroso*, *E. Preciado*, University of California - Riverside, *K. Erickson*, Sandia National Laboratories, *M. Triplett*, University of California - Davis, *C. Lee*, *A. Nguyen*, *I. Lu*, *S. Bobek*, *J. Mann*, University of California - Riverside, *A. Talin*, *F. Leonard*, Sandia National Laboratories, *L. Bartels*, University of California - Riverside

We presents scanning photocurrent measurements on CVD-grown monolayer films of molybdenum disulfide, molybdenum diselenide and the alloys of these materials. Our experiments reveal a pronounced effect of the current on excitation in the gap region between contacts, as opposed to directly at the electrodes. Measurements at different irradiation intensity, irradiation position and bias shed light on the charge transfer processes in

this material system. Thermal effects are ruled out by complementary measurements of thermal transport using infrared imaging.

Thursday Morning, November 13, 2014

Scanning Probe Microscopy Focus Topic

Room: 312 - Session SP+2D+AS+EM+MC+NS+SS-ThM

Probing Electronic and Transport Properties

Moderator: An-Ping Li, ORNL, Corentin Durand, ORNL

8:00am **SP+2D+AS+EM+MC+NS+SS-ThM1 Investigation of the Electronic and Structural Properties of Metal Free Naphthalocyanine Vapor Deposited on Au(111)**, *Bryan Wiggins*, University of Chicago, *K.W. Hipps*, Washington State University

Naphthalocyanines (Ncs) are promising candidates for future components in electronic devices and applications. To maximize the efficiency of Nc devices, it is critical to understand their structural and electronic properties and how these are impacted by deposition methods. The formation of a metal free naphthalocyanine (H_2Nc) self-assembled monolayer on a Au(111) crystal was investigated by scanning tunneling microscopy under ultra-high-vacuum conditions at room temperature. A rigorous purification and processing procedure was developed to produce high purity, low defect, and well-ordered monolayers. High-resolution STM images reveal epitaxial growth of H_2Nc on Au(111) with the observed structure having a molecular spacing of 1.6 ± 0.05 nm, with molecules orientated slightly off (roughly 2.5°) the low density packing direction of Au(111). A commensurate structure having 4 molecules per unit cell and unit cell parameters of $A = 3.25 \pm 0.05$ nm, $B = 3.17 \pm 0.05$ nm, and $\alpha = 87.5 \pm 2^\circ$ is proposed. Orbital-mediated tunneling spectroscopy was used to examine the electronic properties of individual molecules within the thin film. The first ionization potential and electron affinity of H_2Nc adsorbed on Au(111) were measured to be -0.68 ± 0.03 and 1.12 ± 0.02 eV, relative to the Fermi energy.

8:20am **SP+2D+AS+EM+MC+NS+SS-ThM2 The Fundamentals of Charge Transport at Oxide and Ferroelectric Interfaces**, *Ramsey Kraya*, *L.Y. Kraya*, University of Pennsylvania

Here we investigate how charge transport properties at metal-semiconductor interfaces scale down to the nanoscale regime, comparing the properties to macroscopic interfaces and providing a perspective on what it means to device manufacturing. Strontium titanate - the prototypical oxide material - has been widely studied for applications in thermoelectrics, nanoelectronics, catalysis, and other uses, and behaves as an n-type semiconductor when doped. We investigated how charge transport is effected at interfaces to strontium titanate under a wide range of conditions - by varying contact size, interface shape, dopant concentration, and surface structure and in various combinations. The results of the analysis have wide ranging implications, especially for ferroelectric oxide materials and serves as the basis for understanding and controlling switching effects - both polarization and oxygen migration based switching.

8:40am **SP+2D+AS+EM+MC+NS+SS-ThM3 Epitaxial Graphene on Nanostructured Silicon Carbide**, *Phillip First*, Georgia Institute of Technology

INVITED

Graphene grown epitaxially on silicon carbide conforms to nanofaceted step edges, even for step heights of many nanometers. The "sidewall" nanoribbons that result show astounding transport characteristics (~ 15 um ballistic length at room temperature), as demonstrated by others,¹ but the physical basis for these results is still not certain. In our STM measurements of sidewall nanoribbons, we find an extended 1D region with electronic structure much different than 2D graphene. Spectroscopic results on graphene near nanofacet corners indicate a strain gradient and a rapid change in the doping. Such strong gradients may be key to understanding the ballistic transport in this system. P

¹J. Baringhaus, M. Ruan, F. Edler, A. Tejada, M. Sicot, Amina Taleb-Ibrahimi, A.-P. Li, Z. Jiang, E. H. Conrad, C. Berger, C. Tegenkamp and W. A. de Heer, "Exceptional ballistic transport in epitaxial graphene nanoribbons," *Nature*, **506**, 349 (2014).

9:20am **SP+2D+AS+EM+MC+NS+SS-ThM5 Conductivity of Si(111) - 7 x 7: The Role of a Single Atomic Step**, *B. Martins*, University of Alberta and The National Institute for Nanotechnology, Canada, *M. Smeu*, *H. Guo*, McGill University, Canada, *Robert Wolkow*, University of Alberta and The National Institute for Nanotechnology, Canada

The Si(111) - 7×7 surface is one of the most interesting semiconductor surfaces because of its

complex reconstruction and fascinating electronic properties. While it is known that the Si - 7×7 is

a conducting surface, the exact surface conductivity has eluded consensus for decades as measured

values differ by 7 orders of magnitude. Here we report a combined STM and transport measurement

with ultra-high spatial resolution and minimal interaction with the sample, and quantitatively determine the intrinsic conductivity of the Si - 7×7 surface. This is made possible by the capability of

measuring transport properties with or without a single atomic step between the measuring probes:

we found that even a single step can reduce the surface conductivity by two orders of magnitude.

Our first principles quantum transport calculations confirm and lend insight to the experimental

observation.

9:40am **SP+2D+AS+EM+MC+NS+SS-ThM6 Asymmetric Electron Transport Revealed at Monolayer-Bilayer Graphene Junctions by Atomic-Scale Scanning Tunneling Potentiometry**, *K. Clark*, *X. Zhang*, *J. Park*, Oak Ridge National Laboratory, *G. Gu*, University of Tennessee, *G. He*, *R.M. Feenstra*, Carnegie Mellon University, *An-Ping Li*, Oak Ridge National Laboratory

The quest for novel two-dimensional (2D) materials has led to the discovery of hybrid heterostructures of graphene and other 2D atomic films [1]. These heterojunctions provide us fascinating playground for exploring electronic and transport properties in 2D materials. Even in graphene itself, there usually exist large amount of extended topological defects, such as grain boundaries, changes in layer thickness, and substrate steps, which divide graphene into grains and domains. These interfaces and boundaries can break the lattice symmetry and are believed to have a major impact on the electronic properties, especially the transport, in 2D materials.

Here, we present our recent study on an asymmetric electron transport upon bias polarity reversal at individual monolayer-bilayer (ML-BL) boundaries in epitaxial graphene on SiC (0001), revealed by multi-probe scanning tunneling potentiometry [2,3]. A greater voltage drop is observed when the current flows from monolayer to bilayer graphene than in the reverse direction, and the difference remains nearly unchanged when bias exceeds a threshold. A thermovoltage is measured across the boundary due to the thermopower difference between the two sides, which however is too small to account for the observed asymmetry. Interestingly, this asymmetry is not from a typical nonlinear conductance due to electron transmission through an asymmetric potential. Rather, it indicates the opening of an energy gap at the Fermi energy. Our theoretical analysis finds that Friedel charge oscillation opens a gap for electrons with wave vectors perpendicular to the boundary. The Friedel gaps are different on the monolayer and bilayer sides, which can shift under bias and lead to asymmetric transport upon reversing the bias polarity. A quantitative agreement is seen between experiment and theory on both the sign and the magnitude of the asymmetry.

1 "Heteroepitaxial Growth of Two-Dimensional Hexagonal Boron Nitride Templated by Graphene Edges", L. Liu, J. Park, D. A. Siegel, K. F. McCarty, K. W. Clark, W. Deng, L. Basile, J.-C. Idrobo, A.-P. Li, G. Gu, *Science* **343**, 163-167 (2014).

2 "Spatially Resolved Mapping of Electrical Conductance around Individual Domain (Grain) Boundaries in Graphene", K. W. Clark, X.-G. Zhang, I. V. Vlassiouk, G. He, R. M. Feenstra, and A.-P. Li, *ACS Nano* **7** (9), 7956-7966 (2013).

3 "Friedel Oscillation-Induced Energy Gap Manifested as Transport Asymmetric at Monolayer-Bilayer Graphene Boundaries", K. W. Clark, X.-G. Zhang, G. Gu, G. He, R. M. Feenstra, and A.-P. Li, *arXiv*: 1401.1796, *Physical Review X* **4** (1), 011021 (2014).

11:00am **SP+2D+AS+EM+MC+NS+SS-ThM10 Defect-mediated Transport in CVD-grown Monolayer MoS₂**, *Corentin Durand*, *J. Fowlkes*, Oak Ridge National Laboratory, *S. Najmaei*, *J. Lou*, Rice University, *A.P. Li*, Oak Ridge National Laboratory

Transition metal dichalcogenides like molybdenum disulphide (MoS_2) have attracted great interest as candidate to fill the need of 2 dimensional semiconductor materials. By controlling the thickness, the bandgap of MoS_2 thin films can be tuned from 1.2 eV (bulk material, indirect bandgap) to 1.8 eV (monolayer film, direct bandgap). Recently, researchers succeeded in growing monolayered MoS_2 by chemical vapor deposition (CVD) on silicon dioxide (SiO_2) substrate, showing the possibility of low cost scalable device fabrication. However, the mobility reported on exfoliated MoS_2 monolayers exceeds $200 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$, whereas the measurements realized on CVD

growth MoS₂ monolayers reveal a mobility value that is usually 1-2 orders of magnitude lower. Here, we study the transport properties of CVD-grown monolayer on SiO₂/Si substrate. We directly measure the resistivity and the mobility of the material with a field-effect transistor architecture by using a cryogenic four-probe scanning tunneling microscope (STM), the Si substrate being used as back-gate. In order to ensure reliable electrical contacts, we fabricate platinum pads (4x4 μm²) on individual MoS₂ crystal domains by using an electron-beam induced deposition technique. The combination of the STM scanners and a scanning electron microscope (SEM) enables us to connect the STM tips on those pads and thereby establish the contacts on this material without any subsequent lithography process, avoiding contaminations introduced by other technological steps. An electron hopping process in localized charge trapping states appears to dominate the transport behavior. We performed temperature-dependent measurements in the range of 82 K to 315 K which demonstrate a variable range hopping (VRH) transport with a very low mobility. Furthermore, the effects of electronic irradiation are examined by exposing the film to electron beam in the SEM in an ultra-high vacuum environment. We found that the irradiation process affect the mobility and also the carrier concentration of the material, with conductance showing a peculiar time-dependent relaxation behavior. It is suggested that the presence of defects such as vacancies and antisites create charge trapping states, leading to the low mobility. This is consistent with recent density functional theory calculations where these defects are shown to create localized gap states that can act as scattering centers and thereby reduce the mobility.

11:20am **SP+2D+AS+EM+MC+NS+SS-ThM11 Coherent One Dimensional Boundaries in Graphene and Hexagonal Boron Nitride Heterostructures**, *Jewook Park*, Oak Ridge National Laboratory, *L. Liu*, The University of Tennessee Knoxville, *D.A. Siegel*, *K.F. McCarty*, Sandia National Laboratories, *L. Basile*, *J.-C. Idrobo*, *K. Clark*, ORNL, *W. Deng*, The Univ. of Tennessee Knoxville, *C.P. Durand*, ORNL, *G. Gu*, The Univ. of Tennessee Knoxville, *A.P. Li*, ORNL

The quest for novel two-dimensional (2D) materials has led to the discovery of hybrid heterostructures where graphene and other atomic layer films such as monolayer hexagonal boron nitride (hBN) form phase-separated domains or both materials grow epitaxially onto a common crystalline substrate. By implementing the concept of epitaxy to 2D space, we developed and applied a new growth technique to hybrid isostructural but electrically dissimilar materials, such as the 2D epitaxial growth of hBN templated by graphene edge [1]. Scanning tunneling microscopy and spectroscopy measurements revealed a single-atomic-layer, in-plane heterostructure between graphene and hBN, as well as an abrupt 1D zigzag oriented boundary. In addition, the dI/dV conductance map unveiled the 1D interfacial states that are extended along, but localized at the boundary. We investigated spatial and energetic distributions of 1D boundary states. Also, low-energy electron microscopy and micro low-energy electron diffraction confirmed the heterostructure at mesoscopic scale and established that the graphene edge solely determines the crystallography of the hBN regardless of underlying the Cu(100) lattice. The Z-contrast scanning transmission electron microscopy further indicates an atomically sharp interface with a transition width of ~0.5 nm. We suggest that the graphene-hBN epitaxial heterostructure provides an excellent platform to explore heteroepitaxy in 2D space, and the unique functionalities at the 1D interface. [1] Lei Liu *et al. Science* **343** 163 (2014)

11:40am **SP+2D+AS+EM+MC+NS+SS-ThM12 Charge and Spin Density Waves in Quasi One-Dimensional Atomic Wires**, *Herbert Pfnür*, Leibniz Universität, Germany **INVITED**

Although free one-dimensional (1D) objects should exist only at T=0, atomic single wires or arrays embedded into a two- or three-dimensional environment exist even at room temperature and above, since they are stabilized by lateral interactions. These interactions not only stabilize, but also strongly modify the properties of the wires. Their 2D or 3D coupling, however, does not generally prevent observation of 1D properties with their complex variety of instabilities. Furthermore, these coupling can result in special 1D behavior not predicted by standard theories either in 1D or 2D. I will show several examples how atomic wires and wire arrays grown by self-assembly on semiconducting surfaces of Si and Ge acting as insulating substrates can be used to study in detail fundamental aspects of low-dimensional physics, such as charge density waves [1] and Luttinger liquid behavior [2], partially under explicit control of the atomic structure. Due to the low symmetry in these structures, large Rashba-type spin-orbit coupling is expected to lift the spin degeneracy of the metal-induced surface states. In this context new types of spin order were proposed, e.g. for Au/Si(553) [3] and found to be consistent with experiment. As a further example, the Pb/Si(557) system close to monolayer coverage turned out to be an intriguing model system that demonstrates the wealth of phenomena to be expected in quasi-1D physics. Adsorbate induced electronic stabilization leads to (223) refaceting of the (557) surface, to opening of a band gap, to Fermi nesting normal to the steps [4], and to the formation of a charge

density wave. Rashba splitting is so large that it causes in-plane anti-ferromagnetic spin polarization along the steps with twice the step periodicity resulting in a combined spin-charge density wave. New superstructures are formed by an excess Pb coverage up to 0.1ML due to ordered step decoration indicating strong electron-electron correlation across steps. This leads to new long range ordered states and formation of a sequence of 1D charge density waves up to a concentration of 1.5 ML, but also, as very recent angular and spin resolved photoemission studies show, to new ordered spin states.

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[2] C. Blumenstein *et al. Nat. Phys.* **7**, 776 (2011).

[3] S.C. Erwin, F. J. Himpsel, *Nature Communications* **1**, 58 (2010); J. Aulbach *et al. Phys. Rev. Lett.* **111**, 137203 (2013)

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Thursday Afternoon, November 13, 2014

Scanning Probe Microscopy Focus Topic

Room: 312 - Session SP+AS+BI+NS+SS-ThA

Probing Chemical Reactions at the Nanoscale

Moderator: Carl Ventrice, Jr., University at Albany-SUNY, Jun Nogami, University of Toronto, Canada

2:20pm **SP+AS+BI+NS+SS-ThA1 Surface Structures of Catalysts in Reactive Environments with Scanning Tunneling Microscopy.** *Franklin (Feng) Tao, L.T. Nguyen*, University of Notre Dame **INVITED**

Structure and chemistry of catalysts under a reaction condition or during catalysis are the key factors for understanding heterogeneous catalysis. Advance in ambient pressure photoelectron spectroscopy has taken place over the last decades, which can track surface chemistry of catalysts in gas environment of Torr or even tens of Torr pressure range. Environmental TEM has been developed for studying structures of catalysts while they are in a gas or liquid phase. In terms of environmental TEM, images at a pressure up to bars have been obtained although 1-10 Torr to one bar is the typical pressure range of in-situ studies of catalysts by E-TEM. Compared to structural and chemical information of catalyst particles offered from environmental TEM, packing of adsorbed molecules on a catalyst surface and arrangement of catalyst atoms of catalyst surface are complementary for the structure information provided by environmental TEM. High pressure scanning tunneling microscopy (HP-STM) is the most appropriate technique to achieve these pieces of important information. With the HP-STM the structures of surfaces of model catalysts under a reaction condition or during catalysis can be visualized. Surface structures of catalysts only formed under a reaction condition or during catalysis can be tracked. Such information is significant for understanding catalysis performed at solid-gas interfaces.

In this talk, I will present the historical development of HP-STM. Then, I will review the pressure-dependent packing of chemisorbed molecules; one type of pressure dependence is the change of packing of adsorbates from site-specific binding in UHV or a gas phase with a low pressure to non-specific binding in a gas phase at a relatively high pressure; the other type is a switch from one specific binding site to another specific binding site along the increase of the pressure of gas phase of the reactant. In addition, restructuring of a catalyst surface is another consequence of the increase of the gas phase pressure. The threshold pressure at which a restructuring is performed depends on the original surface structure and the intrinsic electronic state of the metal. I will review the surface restructurings of metal model catalysts including different vicinal surfaces in different reactant gases. In addition, the in-situ studies of Pt(110) and Rh(110) during CO oxidation will be taken as two examples to illustrate the in-situ studies of surfaces of metal model catalysts under reaction conditions (in a gas phase of one reactant) and during catalysis (in a mixture of all reactants of a catalytic reaction).

3:00pm **SP+AS+BI+NS+SS-ThA3 Numerical Analysis of Amplitude Modulation Atomic Force Microscopy in Aqueous Salt Solutions.** *P. Karayaylali, Mehmet Z. Baykara*, Bilkent University, Turkey

We present a numerical analysis of amplitude modulation atomic force microscopy in aqueous salt solutions, by considering the interaction of the microscope tip with a model sample surface consisting of a hard substrate and soft biological material through Hertz and electrostatic double layer forces (P. Karayaylali and M.Z. Baykara, *Applied Surface Science*, 2014, DOI: [10.1016/j.apsusc.2014.02.016](https://doi.org/10.1016/j.apsusc.2014.02.016)). Despite the significant improvements reported in the literature concerning contact-mode atomic force microscopy measurements of biological material due to electrostatic interactions in aqueous solutions, our results reveal that only modest gains of ~15% in imaging contrast at high amplitude set-points are expected under typical experimental conditions for amplitude modulation atomic force microscopy, together with relatively unaffected sample indentation and maximum tip-sample interaction values.

3:20pm **SP+AS+BI+NS+SS-ThA4 Surface Potential Investigation of AlGaAs/GaAs Heterostructures by Kelvin Force Microscopy.** *S. Pouch, Nicolas Chevalier, D. Mariolle, F. Triozon, Y.M. Niquet, T. Melin, L. Borowik*, CEA, LETI, MINATEC Campus, France

The Kelvin force microscopy (KFM) provides a spatially resolved measurement of the surface potential, which is related to the energetic band structure of a material. However, it depends strongly on the physical properties of the tip, e.g. width of the apex, the geometric shape and the stiffness of the cantilever as well as the surface sample state. The goal of this work is to investigate the surface potential measured by KFM on

AlGaAs/GaAs heterostructures. For this study, we used a certified reference sample (BAM-L200), which is a cross section of GaAs and $\text{Al}_{0.7}\text{Ga}_{0.3}\text{As}$ epitaxially grown layers with a decreasing thickness (600 to 2 nm) and a uniform silicon doping ($5 \times 10^{17} \text{ cm}^{-3}$). The resulting stripe patterns are commonly used for length calibration and testing of spatial resolution in imaging characterization tools (ToF-SIMS, SEM, XPEEM...). The surface potential measurement is performed under ultra-high vacuum with an Omicron system by using two acquisition modes: the amplitude modulation (AM-KFM), sensitive to the electrostatic force and the frequency modulation (FM-KFM), sensitive to its gradient. Three kinds of tips have been used for this study: platinum or gold nanoparticles coated silicon tips and super sharp silicon tips.

We will present the measurements obtained with these different tips for the narrowest layers (typ. < 40 nm). The surface potential mapping reveals a contrast around 300 meV between $\text{Al}_{0.7}\text{Ga}_{0.3}\text{As}$ and GaAs layers. However, we observed that this contrast vanishes when layer thickness becomes thinner. This loss of contrast cannot be only explained by the resolution limit of the KFM technique. Indeed, we will discuss the effect of the band bending length scale at the AlGaAs/GaAs interface related to the dopant concentration. The contribution of band bending between the layers is evaluated by a self-consistent simulation of the electrostatic potential, accounting for the free carriers distribution inside the sample and for the surface and interface dipoles. We will show that the electric fields of the narrowest layers recover each other, resulting in the partial or total loss of the contrast between $\text{Al}_{0.7}\text{Ga}_{0.3}\text{As}$ and GaAs layers. The simulation results will be compared to the experimental results in order to emphasize that the surface potential contrast is not only influenced by the resolution limit.

4:00pm **SP+AS+BI+NS+SS-ThA6 Probing the Quantum Nature of Hydrogen Bonds at Single Bond Limit in Interfacial Water.** *Ying Jiang*, Peking University, China **INVITED**

Quantum behaviors of protons in terms of tunneling and zero-point motion have significant effects on water properties, structure, and dynamics even at room and at higher temperature. In spite of tremendous theoretical and experimental efforts, accurate and quantitative description of the quantum nuclear effects (QNEs) in water is still challenging, due to the difficulty of accessing the internal degrees of freedom of water molecules. Using a low-temperature scanning tunneling microscope (STM), we are able to resolve in real space the internal structure, that is, the O-H directionality, of individual water molecules adsorbed on a solid surface [1,2]. The key steps are decoupling electronically the water from the metal substrate by inserting an insulating NaCl layer and enhancing the molecular density of states of water around the Fermi level via tip-water coupling. These techniques allow us not only to visualize the concerted quantum tunneling of protons within the H-bonded network, but also to determine the impact of proton delocalization on the strength of hydrogen bonds by resonantly enhanced inelastic electron tunneling spectroscopy (IETS).

Key words: STM, IETS, water, QNEs, proton transfer, H-bonding strength

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4:40pm **SP+AS+BI+NS+SS-ThA8 Resonant Enhanced Spectroscopy of Molecular Rotations with the STM and Field Effect Control of Molecular Dynamics.** *Fabian Natterer, F. Patthey*, Ecole Polytechnique Fédérale de Lausanne (EPFL), Switzerland, *Y. Zhao, J.E. Wyrick, J.A. Stroscio*, NIST, *H. Brune*, Ecole Polytechnique Fédérale de Lausanne (EPFL), Switzerland

Inelastic electron tunneling spectroscopy (IETS) with the scanning tunneling microscope (STM) has vastly fueled the study of magnetic, electronic and vibrational properties of individual atoms and molecules due to its unmatched spatial and excellent energy resolution. Recently [1,2], rotational excitations could be characterized with IETS for the first time and yielded valuable insights into surface dynamics, bond lengths, and, notably about the nuclear spin state of homonuclear molecules. In particular, the two alike nuclei induce symmetry constraints in consequence of the Pauli principle and a certain alignment of nuclear spins requires a specific set of rotational levels J . We demonstrate rotational excitation spectroscopy (RES) with the STM for hydrogen, its isotopes, and mixtures thereof, physisorbed on metal supported graphene and hexagonal boron nitride, as well as on exfoliated graphene devices. We observe excitation energies that are equivalent with rotational transitions ($\Delta J = 2$) of molecules in the gas

phase for hydrogen, hydrogen-deuteride, and deuterium, respectively. Notably, these values represent the nuclear spin isomers *para*-H₂ and *ortho*-D₂. For HD, an additional $J = 0 \rightarrow 1$ transition is discerned, which is allowed for heteronuclear diatomics. We discuss the excitation mechanism in the light of resonant enhanced tunneling [3,4], and illustrate how the dynamics of molecules could be controlled by applying an electric field using a back gating graphene device geometry [5].

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Thursday Evening Poster Sessions

Scanning Probe Microscopy Focus Topic

Room: Hall D - Session SP+AS+EM+NS+SS-ThP

Scanning Probe Microscopy Poster Session

SP+AS+EM+NS+SS-ThP2 Fabrication of Single-Walled Carbon Nanotube Probe and Processing of Single Nanometer Scale Pit with High-Aspect-Ratio of Highly Oriented Pyrolytic Graphite Using by STM, *Syun Ohsumimoto, A. Matsumuro*, Aichi Institute of Technology, Japan

Our unique fabrication methods of high-aspect-ratio nanometer scale three-dimensional structures of pits, lines and convex parts using a multi-wall carbon nanotube (MWNT) with diameter of about 50 nm as a STM probe have been developed successfully. It turns out that this method has been applicable to surfaces of various conducting materials, such as noble metal thin films, low-resistivity single crystalline silicon wafer and highly oriented pyrolytic graphite (HOPG). We also have clarified that the physical origin of this nanometer-scale pit processing using STM must be the field evaporation mechanism by the results of TEM *in-situ* observations during fabrication process. In order to realize further ultra-precise three dimensional structures with high aspect ratio, it is surely required that a innovative ultimate ultra-precision processing technology needs fabrication size below several nm, i.e. single nanometer scale.

This study paid great attention to realize the ultimate processing of single nanometer scale structures using a single-wall carbon nanotube (SWNT) probe as our original STM processing. The most important problem was to overcome to much difficulty in synthesis of SWNT probes with high probability. Then, the application of mixed dispersion liquid containing both MWNTs and SWNTs could be devised at the process of producing SWNT probes. In this process, it was clarified that the SWNT easily attached to the point of the MWNT, which was easily adhered to the apex of the conventional tungsten needle through the pulling method that we developed originally. The success rate for synthesis of the SWNT probes with diameters of about 2 nm and 10 nm were drastically increased up to about 10 % and 14 %, respectively. As compared with the case where the dispersion liquid of only SWNT is used, success fabrication rate has been nearly equal to 0 %. Single nanometer scale pits were actually fabricated on HOPG in atmosphere and room temperature condition. The SWNT probe with diameter of about 2 nm under the conditions of a bias voltage of 5 V, tunnel current of 1 nA and fabrication time of 60 s could realize a single nanometer scale pit with the diameter of 9 nm and the depth of 13 nm. The aspect ratio with SWNT probes increased up to about 5 times in the case of MWNT probes. These demonstrate that these STM fabrications by using SWNT probes with several diameters must give a remarkable effect in fabricating three-dimensional high-aspect-ratio structures with single nanometer-scale.

SP+AS+EM+NS+SS-ThP3 Probing the Electronic Structure of the Layered Electride Ca_2N , *Jeonghoon Ha*, NIST/Maryland Nano Center, University of Maryland, *H. Baek*, NIST & Seoul National University, Republic of Korea, *D. Zhang*, NIST/Maryland Nano Center, University of Maryland, *Y. Kim, S. Kim, Y.J. Song*, Sungkyunkwan University, Republic of Korea, *Y. Kuk*, Seoul National University, Republic of Korea, *J.A. Stroscio*, NIST

Electrides are electronic materials in which excessive electrons are confined into cavities defined by the crystal structure. These excessive electrons take the place of negatively charged ions in an ionic crystal. The geometry of the cavities confining these anionic electrons determines the electronic properties of the material and provides a platform to study various interaction physics [1]. A previous study reported the inorganic electride Ca_2N to have a layered structure with anionic electrons confined to 2-dimensional cavities between the cationic crystal layers [2]. In this previous study, transport measurements showed high electron mobility and long mean scattering time, and magneto-resistance measurements confirmed diffusive 2-dimensional transport in the electron layers.

In the present work, we use an ultra-low temperature scanning tunneling microscope to investigate the local electronic structure of a cleaved surface of a Ca_2N single crystal. An energy gap was observed in the tunneling spectrum with a gap size of 0.4 meV. The spectra contain multiple coherence-like peaks which are equally spaced in energy, suggestive of possible multi-band superconductivity or quantum confinement in the electron layers. Temperature-dependent tunneling spectroscopy measurements show a gradual suppression of the energy gap up to 2.5 K. An interesting observation is that the gap structure and the peak features do not get suppressed in the presence of a perpendicular magnetic field up to

14.5 T, suggesting if the crystal is in a superconducting state, then the critical field is extremely large compared to the transition temperature. These observations and further discussion of possible unconventional superconductivity will be discussed in this presentation.

[1] J. Dye, *Science* **301**, 607 (2003)

[2] K. Lee *et al.*, *Nature* **494**, 336 (2013)

SP+AS+EM+NS+SS-ThP5 Improving the Accuracy of Atomic Force Microscopy in Nanometrology for Linewidth Measurements, *James Su, N.N. Chu, M.H. Shiao, C.N. Hsiao*, Instrument Technology Research Center, National Applied Research Laboratories, Taiwan, Republic of China

Atomic force microscopy (AFM) has an important role in dimensional metrology especially in the nanoscale. The morphology image processed by the AFM is the interaction between the tip and the sample surface. The result of the interaction may cause broadening of peaks and shrinking of valleys in the scanning process caused by tip effects. It would be impossible to differentiate the portion due to the tip and the portion due to the sample surface without determining the tip geometry which is a key role in AFM-image quality. As a case study, AFM measurements of nanowires (NW), carbon nanotubes (CNT) and nano-honeycombs fabricated by nanosphere lithography (NSL) technology are examined. Line width measurement results may expand up to 39.5% by adopting a conventional pyramid-shaped probe and 17.5% by using a conical-shaped one as the dimensions of the scanned features approaches to the order of magnitude of the tip apex. The uncertainty of measurement would expand if tip wear occurs during image scan. Calculation for surface reconstruction has been developed to extract the part related to the tip from the SPM image. The SPM used for these measurements is equipped with a highly accurate scanning system, which employs closed-loop capacitive feedback control to ensure outstanding linearity and position accuracy. To identify the geometry of the tip, a silicon tip characterization grating was imaged between the measurements. Deconvolution process were carried out for topography image corrections, and the results were further compared with the ones measured from the scanning electron microscope (SEM). This process is essential to derive accurate measurement results in the nanoscale region.

SP+AS+EM+NS+SS-ThP8 The Effect of Electrochemical Potential on Single Molecule Conductance, *Esteban Sanchez, R. Aguilar*, BUAP, Mexico, *S. Afsari*, Temple University, *Z. Li*, Ball State University, *E. Borguet*, Temple University

Porphyryns have been widely studied for their electrochemical properties to understand charge transfer. The related property of charge transport can be accessed by single molecule conductance (SMC) measurements. The most common SMC studies involve transport between different anchor groups at transversal positions in the molecule [1]. Few investigations have been made using porphyryns lying flat on the substrate in electrochemical environment [2]. Recent studies have shown that the templating effect of self-assembly can be exploited to orient molecules in metal-molecule-metal junctions, so that transport perpendicular to the molecular plane can also be easily accessed [3].

This goal research is to use self assembly, verified by scanning tunneling microscopy (STM), to measure charge transport in single porphyryns adsorbed flat on the Au (111) surface. 5,10,15,20-Tetra(4-pyridyl)porphyrin (TPyP) is a good candidate for this research because it has been demonstrated that this porphyrin has a strong interaction with, and can form ordered layers on, Au (111) in electrochemical environment [4]. This control of the orientation of the porphyrin by electrochemical potential enables us to make SMC measurements perpendicular to the molecular plane.

[1] Zhihai Li, Manuel Smeu, Mark A. Ratner, and Eric Borguet, Effect of Anchoring Groups on Single Molecule Charge Transport through Porphyryns, *J. Phys. Chem. C*, **117**, 14890–14898 (2013).

[2] Quirina Ferreira, Ana M. Braganca, Luis Alcacer, and Jorge Morgado, Conductance of Well-Defined Porphyrin Self-Assembled Molecular Wires up to 14 nm in Length, *J. Phys. Chem. C*, **118**, 7229–7234 (2014)

[3] Sepideh Afsari, Zhihai Li, and Eric Borguet, Orientation-Controlled Single-Molecule Junctions, *Angew. Chem. Int. Ed.* **53**, 9771–9774 (2014).

[4] Tao Ye, Yufan He, and Eric Borguet, Adsorption and Electrochemical Activity: An In Situ Electrochemical Scanning Tunneling Microscopy Study of Electrode Reactions and Potential-Induced Adsorption of Porphyryns, *J. Phys. Chem. B*, **110**, 6141–6147 (2006).

Friday Morning, November 14, 2014

Scanning Probe Microscopy Focus Topic

Room: 312 - Session SP+AS+BI+EM+NS+SE+SS-FrM

Probe-Sample Interactions and Emerging Instrument Formats

Moderator: Carl Ventrice, Jr., University at Albany-SUNY

8:40am **SP+AS+BI+EM+NS+SE+SS-FrM2 2013 ASSD Student Award Talk: New Insights into Nanoscale Adhesion from *In Situ* TEM Studies**, Tevis Jacobs, J.A. Lefever, University of Pennsylvania, J. Liu, University of Wisconsin-Madison, D.S. Grierson, SysteMECH LLC, K.E. Ryan, P.L. Keating, J.A. Harrison, United States Naval Academy, K.T. Turner, R.W. Carpick, University of Pennsylvania

A fundamental understanding of adhesion is important for applications at all length scales, but is particularly critical in nanoscale devices and applications due to their high surface-to-volume ratio. Advancements in studying such tribological phenomena are typically hindered by the inaccessibility of the sliding interface. We will present nanoscale adhesion measurements conducted inside of a transmission electron microscope (TEM), using a modified *in situ* nanoindentation apparatus that makes contact with atomic force microscope (AFM) cantilever tips. This tool provides new opportunities to observe, identify, and quantify tribological processes with unprecedented access and resolution. First, using ultra-strong carbon-based tip materials, we find that roughness of tips can greatly reduce the pull off force and lead to severe underestimation of the work of adhesion [1]. Furthermore, we have quantified adhesion by making and breaking contact between nanoscale silicon asperities and a flat diamond substrate. The snap-in distance and the pull-off force are measured with sub-nanometer and sub-nanonewton resolution, respectively. The shape of the Si asperity is determined with sub-nanometer resolution immediately before and after contact to verify that elastic conditions were maintained. From this, we independently determine the work of adhesion and range of adhesion. The results show that accounting for roughness has a strong effect on both parameters. These two results demonstrate the importance of applying *in situ* approaches to studies of adhesion. --- I. Jacobs, T.D.B., Ryan, K.E., Keating, P.L., Grierson, D.S., Lefever, J.A., Turner, K.T., Harrison, J.A. and Carpick, R.W. The Effect of Atomic-Scale Roughness on the Adhesion of Nanoscale Asperities: A Combined Simulation and Experimental Investigation. *Tribol. Lett.* 50, 81-93 (2013).

9:40am **SP+AS+BI+EM+NS+SE+SS-FrM5 Nanoscale Mapping of the W/Si(001) Schottky Barrier using Ballistic Electron Emission Microscopy**, Christopher Durcan, University of Albany-SUNY, V.P. LaBella, University at Albany-SUNY

The W/Si(001) Schottky barrier was spatially mapped using ballistic electron emission microscopy (BEEM) and ballistic hole emission microscopy (BHEM) using high resistivity *n*-type and *p*-type silicon substrates. A thin tungsten silicide is observed upon deposition utilizing transmission electron microscopy (TEM) and Rutherford backscattering spectrometry (RBS). The sum of the Schottky barrier heights from *n*-type and *p*-type silicon substrates agree with the silicon band gap. The BEEM and BHEM spectra are fit utilizing a linearization method to the power law of the BEEM model. Spatially resolved Schottky barrier maps are generated over a 1 μ m x 1 μ m area and provide insight into the spatial homogeneity of the barrier height. Histograms of the barrier heights show a Gaussian distribution, consistent with an interface dipole model.

10:00am **SP+AS+BI+EM+NS+SE+SS-FrM6 Local Probing of Superconductivity in Half Heusler Compounds**, Hongwoo Baek, NIST & Seoul National University, Republic of Korea, J. Ha, D. Zhang, NIST/Maryland Nano Center, University of Maryland, Y. Nakajima, P.S. Syers, X. Wang, K. Wang, J. Paglione, University of Maryland, Y. Kuk, Seoul National University, Republic of Korea, J.A. Stroscio, NIST

Heusler alloys have attracted interest as multifunctional experimental platforms for topological quantum phenomena ranging from magnetism to superconductivity and heavy fermion behavior. The rare-earth chalcogenide ternary half Heusler compounds were theoretically predicted to have topologically nontrivial surface states due to band inversion [1]. The lack of inversion symmetry of the crystal lattice makes unconventional pairing symmetry feasible. The superconductivity in the non-centrosymmetric half Heusler compound YPtBi was recently reported as a promising system for the investigation of topological superconductivity [2]. In this work, we use ultra low temperature scanning tunneling microscopy to investigate the superconducting properties of the ternary half Heusler compounds YPdBi and YPtBi. Both were theoretically proposed to have topological states with

different band inversion strength [1], and experimentally reported as a topological insulator [3]. Strong spin-orbit coupling and the lack of inversion symmetry present the possibility of spin-triplet superconductivity in these materials. The tunneling spectra of YPdBi show two different superconducting gaps of 0.36 meV and 0.16 meV depending on the measurement location. The variation in gaps might originate from inhomogeneity in the crystal. The superconducting gap of 0.36 meV is completely suppressed above a critical magnetic field of $B=2.5$ T, in agreement with bulk transport measurements. A superconducting gap of 0.21 meV and an upper critical field of 1.25 T were measured in a circular superconducting domain of diameter ≈ 180 nm in YPtBi. Sequential addition of single vortices to the superconducting YPtBi domain could be observed with increasing magnetic field, with vortices occupying the perimeter of the island. These observations will be discussed in terms of island confinement and pairing symmetry of YPtBi.

[1] S. Chadov, X. Qi, J. Kubler, G. H. Fecher, C. Felser, and S. C. Zhang, *Nat. Mater.* **9**, 541 (2010).

[2] N. P. Butch, P. Syers, K. Kirshenbaum, A. P. Hope, and J. Paglione, *Phys. Rev. B* **84**, 220504(R) (2011).

[3] W. Wang, Y. Du, G. Xu, X. Zhang, E. Liu, Z. Liu, Y. Shi, J. Chen, G. Wu, and X. Zhang, *Scientific Reports* **3** (2013).

10:40am **SP+AS+BI+EM+NS+SE+SS-FrM8 Multimodal Intermittent Contact Atomic Force Microscopy: Topographical Imaging, Compositional Mapping, Subsurface Visualization and Beyond**, Santiago Solares, George Washington University

Multifrequency atomic force microscopy (AFM) refers to a family of techniques that involve excitation of the microcantilever probe at more than one frequency [R. Garcia and E.T. Herruzo, *Nature Nanotechnology* **7**, 217 (2012)]. This can be carried out in a sequential manner, varying the excitation frequency over time, as in chirp band excitation methods, or simultaneously supplying drive signals containing more than one frequency to the cantilever shaker. The latter mode of operation commonly involves the simultaneous excitation of more than one cantilever eigenmode, such that each eigenmode is used to carry out different functions. For example, in a recently developed trimodal imaging scheme for soft sample characterization [D. Ebeling, B. Eslami and S.D. Solares, *ACS Nano*, **7**, 10387 (2013)], the fundamental eigenmode is used for topographical acquisition, as in standard tapping-mode AFM, while two higher eigenmodes are used for compositional mapping and subsurface visualization, respectively. This talk presents experimental and computational results for validated multimodal imaging schemes involving one to three eigenmodes, and discusses the expected benefits and complexities of including more than three eigenmodes.

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Turner, K.T.: SP+AS+BI+EM+NS+SE+SS-FrM2, 11
Tyagi, P.: 2D+AS+HI+MC+NS+PS+SP+SS-TuA10, 2
— **V** —
Ventrice, Jr., C.A.: 2D+AS+HI+MC+NS+PS+SP+SS-TuA10, 2
— **W** —
Wang, K.: SP+AS+BI+EM+NS+SE+SS-FrM6, 11
Wang, X.: SP+AS+BI+EM+NS+SE+SS-FrM6, 11

Wiggins, B.C.: SP+2D+AS+EM+MC+NS+SS-ThM1, 6
Wolkow, R.: SP+2D+AS+EM+MC+NS+SS-ThM5, 6
Wyrick, J.E.: SP+AS+BI+NS+SS-ThA8, 8
— **Y** —
Yang, Y.: SP+AS+BI+NS+SS-WeA10, 5
Yeom, H.W.: SP+AS+BI+NS+SS-WeA7, 4; SP+AS+BI+NS+SS-WeA9, 5
Yoshizawa, S.: SP+AS+BI+NS+SS-WeA3, 4
Yu, Y.: 2D+AS+HI+MC+NS+PS+SP+SS-TuA4, 1
— **Z** —
Zhang, D.: SP+AS+BI+EM+NS+SE+SS-FrM6, 11; SP+AS+EM+NS+SS-ThP3, 10
Zhang, X.: SP+2D+AS+EM+MC+NS+SS-ThM6, 6
Zhao, Y.: SP+AS+BI+NS+SS-ThA8, 8
Zhou, G.W.: IS+2D+MC+NS+SP+SS-WeA9, 3